

Features

- Freq: 6~18GHz
- Isolation: 20dB
- Insertion Loss: 0.8dB
- Chip Size: 1.025mm×0.925mm×0.1mm

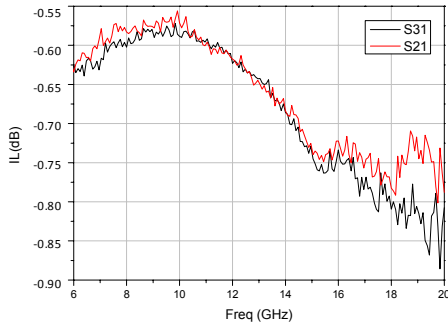
General Description

The HG126GB is a 2-way GaAs pHEMT power divider that is operating from 6 to 18 GHz. This chip features very high isolation of 20dB and extremely low insertion loss of 0.8dB. Input and Output VSWR are 1.6/1.4.

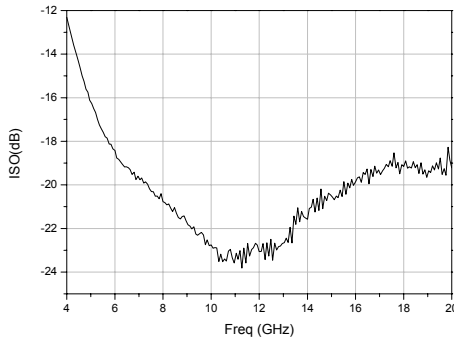
Electrical Specifications (T_A=25 °C)

Parameter	Min.	Typ.	Max.
Frequency Range(GHz)	6~18		
Input VSWR	-	1.6	-
Output VSWR	-	1.4	-
Insertion Loss(dB)	-	0.8	-
Isolation (dB)	-	20	-

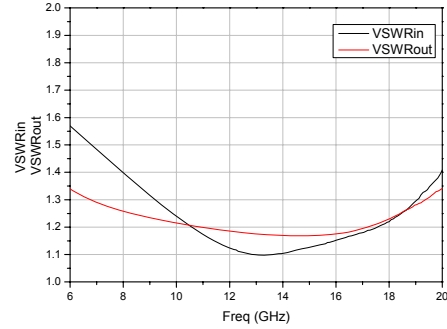
Insertion Loss



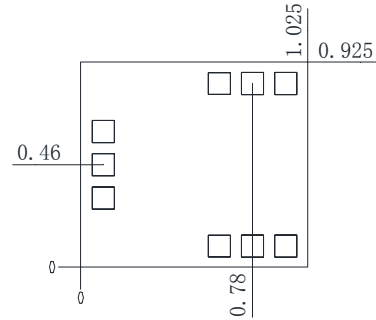
Isolation



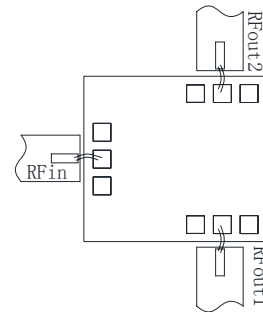
Input and Output VSWR



Outline Drawing (mm)



Assembly Diagram



Absolute Maximum Ratings

RF Input Power	+27dBm
Operating Temperature	-55°C~125°C
Storage Temperature	-65°C~150°C

Notes:

1. The chip should be stored in a dry and nitrogen environment, and used in a clean environment.
2. GaAs material is brittle, can not touch the surface of the chip, must be careful when using.
3. The chip is welding with conductive adhesive or alloy (alloy temperature should not exceed 300°C, and no more than 30 sec.), and should make it fully grounded.
4. The chip microwave port and substrate gap is not exceeding 0.05mm, with Φ25μm double gold wire bonding, suggested length of gold wire 250~400μm.
5. Chip microwave port without DC blocking capacitor.
6. The chip is sensitive to static electricity, and should be protected against static electricity during storage and use.